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Applicant: V. Vaganov

Group Art Unit: 2878

Serial No.: 09/596,837

Examiner: G. Goudreau

Filed: 06/19/2000

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No.: SS-714-01

OFFICIAL

For: METHOD FOR FABRICATING MICROSTRUCTURES WITH  
DEEP ANISOTROPIC ETCHING OF THICK SILICON WAFERSCOMMISSIONER FOR PATENTS  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date of this Paper:

November 18, 2003AMENDMENT

In response to the U.S. Patent and Trademark Office Action mailed 07/30/03, please amend the above-identified application as follows: